

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/670928	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 09:37
L2	940	strained near3 silicon	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 10:38
L3	6	strained near3 silicon adj nitride	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 09:38
L4	1248	("SOI" semiconductor adj on adj insulator) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 10:40
L5	359	4 and (crystal\$5) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 10:41
L6	44	5 and (nitridation nitrify nitrification silicide silicidation oxynitridation) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 10:44
L7	118	5 and (implant\$4 nitridation nitrify nitrification silicide silicidation oxynitridation) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 13:52
L8	147	5 and (implant\$4 nitridation nitrify nitrification silicide silicidation oxynitridation oxidation) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 13:52
L9	1	8 and (stained) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 13:53

L10	99	8 and (strained) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 14:58
L11	19	10 and (nitride) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 15:18
L12	0	10 and (oxynitride) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/13 15:18

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S29	6	"6524935"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 08:40
S30	862	("SiGe" 'sige' silicon near3 geranium) with (strained relaxed)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:04
S31	632	S30 and (implant\$3 nitridation nitrify nitrification inject\$3 silicide silicidation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:02
S32	632	S30 and (implant\$3 nitridation nitrify nitrification inject\$3 silicide silicidation oxynitridation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:03
S33	175	S32 and ("SiGe" 'sige' silicon near3 geranium) with (crystalline ((mono single) near3 (crystal crystalline)))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:07
S34	166	S33 and ("SiGe" 'sige' silicon near3 geranium) with ('soi' insulat\$3 substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:08
S35	166	S34 and (nitride silicon oxynitride nitrogen germanium metal metal\$4 heat\$3 anneal\$3 oxide)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 10:16
S37	1	S35 and vacan\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:12
S38	95	S35 and \$4nitrid\$7	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08
S39	10	"6455398"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08

BRS:

Pending

Active

- L1: (1) 10/670928
- L3: (6) strained near3 silicon adj nitride
- L2: (940) strained near3 silicon
- L4: (1248) ("SOI" semiconductor adj on adj insulator) with (silicon adj germanium 'sige')
- L5: (359) 4 and (crystal\$5) with (silicon adj germanium 'sige')
- L6: (44) 5 and (nitridation nitrify nitrification silicide silicidation oxynitridation) with (sil...
- L7: (118) 5 and (implant\$4 nitridation nitrify nitrification silicide silicidation oxynitridation...
- L8: (147) 5 and (implant\$4 nitridation nitrify nitrification silicide silicidation oxynitridation...
- L9: (1) 8 and (stained) with (silicon adj germanium 'sige')
- L10: (99) 8 and (strained) with (silicon adj germanium 'sige')
- L11: (19) 10 and (nitride) with (silicon adj germanium 'sige')
- L12: (0) 10 and (oxynitride) with (silicon adj germanium 'sige')
- L13: (125) (oxynitride) with (silicon adj germanium 'sige')

Failed

Search List Browse Query Clear
 DBs: JIS-PG-PUB, US-PAT, EPO, IPO ☒ Basic
 Default operator: OR ☐ Highlight all hit terms initially
 (oxynitride) with (silicon adj
 germanium 'sige')

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3
1	<input type="checkbox"/>	US 2005012	2005060	27	Semiconductor device an	438/197			Kanemoto, Kei	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 2005011	2005060	13	Dielectrics with improved	438/786			Chou, Anthony I. et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 2005008	2005042	8	Multi-layer dielectric con	438/763			Adetutu, Olubummi	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 2005008	2005042	18	Surface engineering of na	427/212	427/372.2		Yadav, Tapeshe et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 2005006	2005033	12	Memory cell with nanocr	257/390	257/321;		Gutsche, Martin et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	US 2005006	2005032	35	Process for deposition of	438/478			Todd, Michael A. et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	US 2005005	2005031	13	Semiconductor device wit	438/260			Steimle, Robert F. e	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
8	<input type="checkbox"/>	US 2005005	2005031	19	Organic electronic device	313/503	313/504;		Yu, Gang et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>